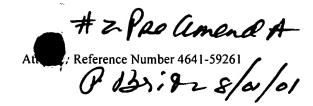
DLS:fam 06/13/01 PATENT



#### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Ushio et al.

Application No. New Application

Filed: Herewith

For: LAYER-THICKNESS DETECTION METHODS

AND APPARATUS FOR WAFERS AND THE

LIKE, AND POLISHING APPARATUS

Examiner: (Unknown)

Date: June 13, 2001

BOX PATENT APPLICATION COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231 Art Unit: (Unknown)

#### **CERTIFICATE OF MAILING**

I hereby certify that this paper and the documents referred to as being attached or enclosed herewith are being deposited with the United States Postal Service on June 13, 2001 as First Class Mail in an envelope addressed to: BOX PATENT APPLICATION, COMMISSIONER FOR PATENTS, WASHINGTON, D.C. 20231.

Attorney for Applicant

### PRELIMINARY AMENDMENT

Please amend the subject application as follows:

## In the Specification:

Please add on page 1, before "Field of the Invention":

AI

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Q)

T. .....

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# **Cross-Reference to Related Application**

This application is a divisional of co-pending U.S. Patent application no. 09/316,082, filed on May 20, 1999.

Replace the paragraph starting at page 1, lines 27-31, and ending at page 2, lines 1-8, with the following paragraph:

AZ lont'd Responsive to the need to achieve ever-increasing device density along with ever-decreasing feature sizes, the microlithography industry has developed microlithography apparatus that utilize extremely short wavelengths of light, such as deep-UV light, but at large numerical apertures. Projection optics used in such apparatus have extremely short focal ranges. The focal ranges are now so short that the uneven surface that results from stacking multiple